MICROWAVE POWER GaAs FET

FEATURES

- •BROAD BAND INTERNALLY MATCHED FET •HIGH POWER P1dB= 48.0dBm at 7.7GHz to 8.5GHz
- P10B= 48.00Bm at 7.7GHz to 8.5

HIGH GAIN

G1dB= 7.5dB at 7.7GHz to 8.5GHz

- ·LOW INTERMODULATION DISTORTION
- IM3(MIN.)= -25dBc at Pout= 41dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE

MICROWAVE SEMICONDUCTOR TECHNICAL DATA



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.	
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 9.5A f= 7.7 to 8.5GHz	dBm	47.0	48.0	_	
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.5	7.5	_	
Drain Current	IDS1		А		14.5	16.0	
Gain Flatness	ΔG		dB			±0.8	
Power Added Efficiency	ηadd		%		36		
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 41dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-25	-30		
Drain Current	IDS2		А			13.1	
Channel Temperature Rise	∆Tch	$(VDS \times IDS + Pin - P1dB) \times Rth(c-c)$	°C			100	

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 11.0A	S	_	15.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 120mA	V	-1.0	-1.8	-2.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А		27	
Gate-Source Breakdown Voltage	VGSO	IGS= -0.4mA	V	-5	_	
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		0.8	1.0

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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20.0
Total Power Dissipation (Tc= 25°C)	PT	W	150
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA09A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaAs FET TIM7785-60ULA

TYPICAL RF PERFORMANCE

·Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 9.5 A, f= 7.7, 8.1, 8.5 GHz, Ta= +25 °C







MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·IM3, IM5 vs. Pout

VDS= 10 V, IDSset= 9.5 A, f= 7.7, 8.1, 8.5 GHz, Δf= 5 MHz , Ta= +25 °C



·IM3, IM5 vs. Pout

VDS= 10 V. IDSset= 8.5. 9.5. 10.5 A. f= 8.1 GHz. Ta= +25 °C



MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·S-Parameters

VDS= 10 V, IDSset= 9.5 A, f= =6.0 to 9.5 GHz, Ta= +25 °C







MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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